SILICON MIXER DIODE

DESCRIPTION:

The **ASI 1N21WE** is a Silicon Mixer Diode Designed for Applications Operating From 8.0 to 12.4 GHz.

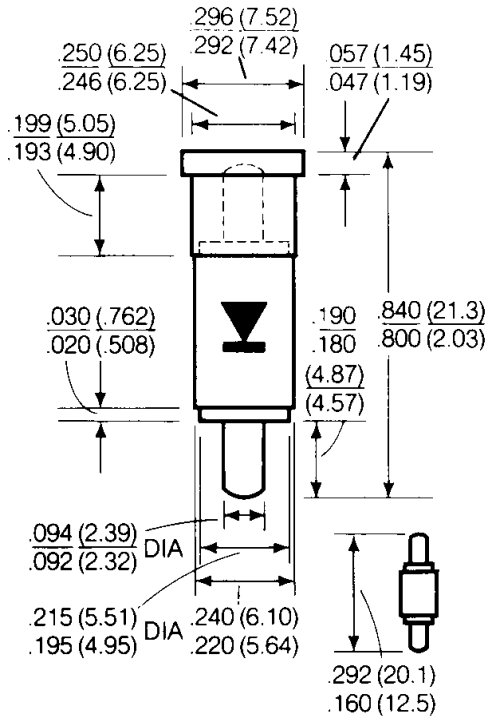
FEATURES:

- High burnout resistance
- Low noise figure
- Hermetically sealed package

MAXIMUM RATINGS

I_F	20 mA
V_R	1.0 V
P_{DISS}	5.0 (ERGS) @ T_C = 25 ^{O}C
T_J	-55 ^{O}C to +150 ^{O}C
T_{STG}	-55 ^{O}C to +150 ^{O}C

PACKAGE STYLE DO- 23



CHARACTERISTICS T_C = 25 ^{O}C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIM	UNITS
N_F	F = 3060 MHz P_{lo} = 0.5 mW N_{Fif} = 1.5 dB R_L = 100 Ω I_F = 30 MHz			7.0	**dB**
V_{SWR}				1.3	
Z_{IF}	R_L = 22 Ω f = 1000 Hz	350		450	**Ω**
frange		8.0		12.4	**GHz**

Specifications are subject to change without notice.

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